4-BIT SINGLE-CHIP MICROCONTROLLER

The μPD17P107 is a tiny microcontroller composed of a ROM with 1K-byte capacity, a RAM with 16-word capacity and 11 I/O ports. It is a product developed by replacing the on-chip mask ROM of the μPD17107 with the one-time PROM.

The μPD17P107CX, which is writable only once, and the μPD17P107GS are available. They are convenient for evaluating or producing in small quantities the μPD17107.

Very efficient programming is possible due to the μPD17000 architecture incorporating the general-purpose register system, which allows the data memory to be manipulated directly, being adopted in the CPU. Every instruction is composed of 1 word of 16-bit length.

FEATURES

- μPD17107 compatible
- Program memory (one-time PROM): 1K byte (512 words × 16 bits)
- Data memory (RAM): 16 words × 4 bits
- I/O ports: 11 ports (N-ch open-drain output 3 ports)
- Instruction execution time: 128 μs (62.5 kHz) to 8 μs (1 MHz)
- Instruction types: 24 types (all 1-word instructions)
- Stack levels: 1 level
- Standby function available (by STOP, HALT instruction)
- Data memory data retainable at low voltage (MIN. 2.0 V)
- With on-chip system clock oscillator (only resistor externally provided)
- Operating supply voltage: 2.5 to 6.0 V (at 250 kHz)
  4.5 to 6.0 V (at 1 MHz)

APPLICATIONS

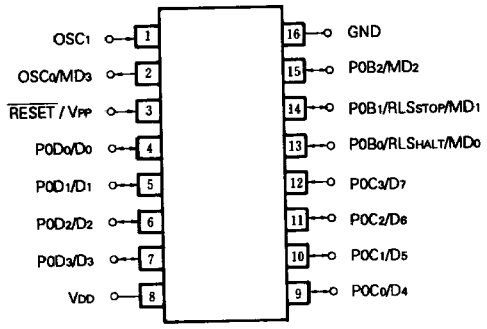
- Electronic control of home electric appliances, TOY, etc.

ORDERING INFORMATION

Order Code	Package
μPD17P107CX	16-pin plastic DIP (300 mil)
μPD17P107GS	16-pin plastic SOP (300 mil)

PIN CONFIGURATION (Top View)

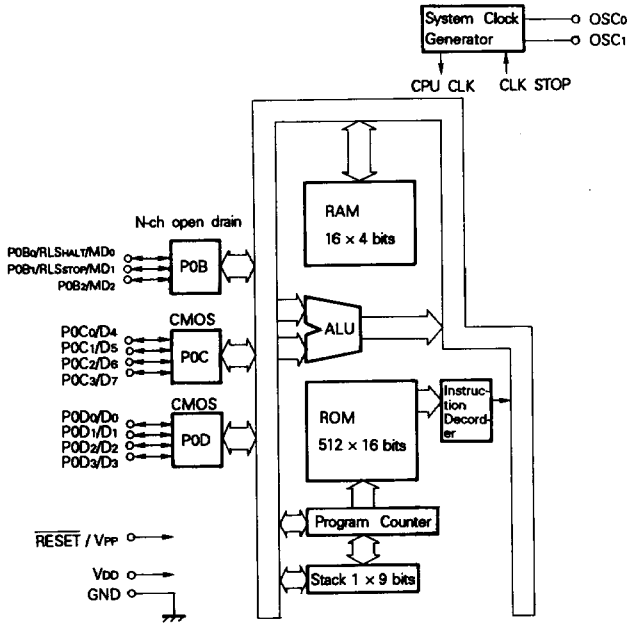
μPD17P107CX/μPD17P107GS



16 Pin Plastic DIP

16 Pin Plastic SOP

BLOCK DIAGRAM



PIN FUNCTIONS

PIN FUNCTION LIST

- Port pins

Pin Name	Input/ Output	Dual-Function Pin		Function		Program Memory Write/Verify Mode	Reset
P0B0	Input/ Output	RLSHALT	MD0	• N-ch open-drain 4-bit input/ output port (Port 0B)	HALT mode releasing	Mode setting pin	High impedance (input mode)
P0B1		RLSSTOP	MD1		STOP mode releasing		
P0B2		MD2					
P0C0	Input/ Output	D4		• CMOS (push-pull) 4-bit input/output port (Port 0C)		8-bit data input/ output pin (high-order 4 bits)	High impedance (input mode)
P0C1		D5					
P0C2		D6					
P0C3		D7					
P0D0	Input/ output	D0		• CMOS (push-pull) 4-bit input/output port (Port 0D)		8-bit data input/ output pin (low-order 4 bits)	High impedance (input mode)
P0D1		D1					
P0D2		D2					
P0D3		D3					

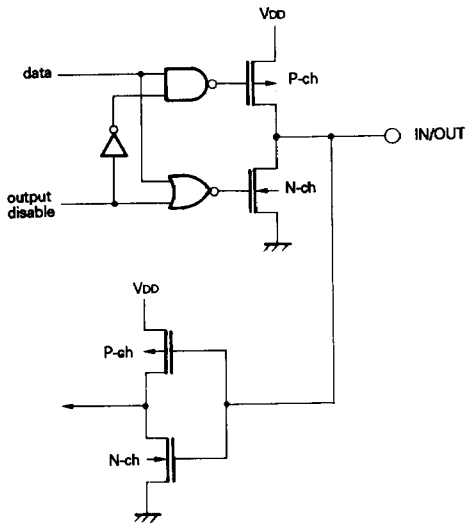
- Other than port pins

Pin Name	Input Output	Dual-Function Pin	Function	Program Memory Write/Verify Mode
$\overline{\text{RESET}}$	Input	VPP	System reset input pin	Voltage impression pin (+12.5 V)
VDD			Positive power pin	Positive power pin (+6.0 V)
GND			GND pin	GND pin
OSC1			System clock oscillation resonator connection pin	Program memory address update
OSC0		MD3	System clock oscillation resonator connection pin	Mode setting pin

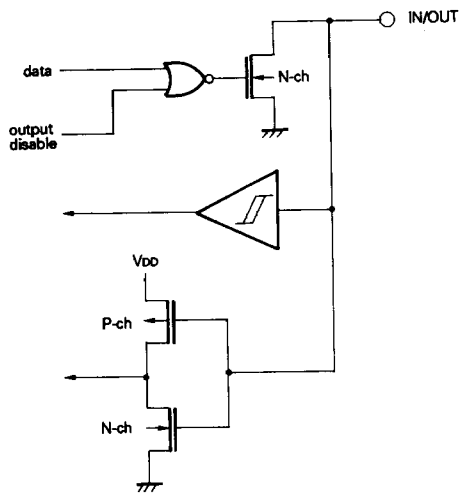
PIN INPUT/OUTPUT CIRCUITS

The μPD17P107 pin input/output circuit diagrams are shown below.

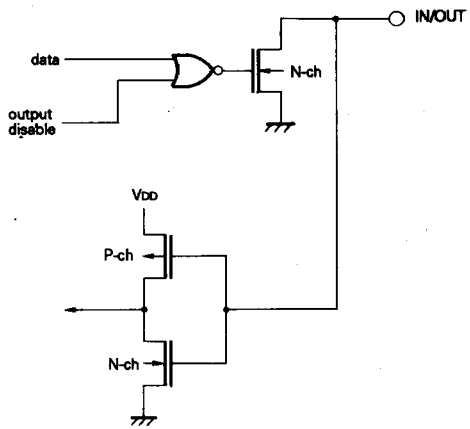
(1) P0C, P0D



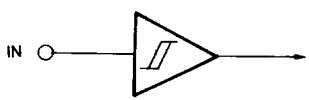
(2) P0B0, P0B1



(3) $P0B_2$



(4) $\overline{RESET}$



9. DIFFERENCES BETWEEN μPD17P107 AND μPD17107

The μPD17P107 is a product developed by replacing the program memory of the μPD17107 with the on-chip mask ROM with the one-time PROM. These 2 models have the same CPU functions and on-chip hardware with the only difference being the program memory and the mask option. Table 9-1 shows the differences between the μPD17P107 and μPD17107.

Table 9-1 Differences between μPD17P107 and μPD17107

Item	μPD17P107	μPD17107
ROM	One-time PROM 512 × 16 bits	Mask ROM 512 × 16 bits
$P0B_0$ to $P0B_2$ pin pull-up resistor	Not available	Mask option
$\overline{RESET}$ pin pull-up resistor	Not available	Mask option
Connection pin	V_{PP} pin, run mode selection pin available	V_{PP} pin, run mode selection pin not available
Input power	2.5 to 6.0 V (at 250 kHz) 4.5 to 6.0 V (at 1 MHz)	
Package	16-pin DIP 16-pin SOP	

10. ONE-TIME PROM (PROGRAM MEMORY) WRITE AND VERIFY

The μPD17P107's on-chip program memory is a 512 × 16-bit one-time PROM.

To write/verify this one-time PROM, the pins shown in the table below are used. No address input is available. Instead, a system to update the address by the clock input via the OSC_1 pin is adopted.

Pin Name	Function
V_{PP}	Voltage impression pin at program memory write/verify
OSC_1	Address updating clock input pin at program memory write/verify
MD_0 to MD_3	Input pin at program memory write/verify. Used as run mode selection pin.
D_0 to D_7	8-bit data input/output pin at program memory write/verify

10.1 RUN MODE AT PROGRAM MEMORY WRITE/VERIFY

The μPD17P107 assumes the program memory write/verify mode if +6 V is impressed to the V_{DD} pin and +12.5 V is impressed to the V_{PP} pin after the reset status (V_{DD} = 5 V, $\overline{RESET}$ = 0 V) assumed for a certain period of time. In that mode, the following run mode is entered according to the MD_0 to MD_3 pin setting. All the remaining pins are at the GND potential by the pull-down resistor.

Run Mode Setting						Run Mode
V_{PP}	V_{DD}	MD_0	MD_1	MD_2	MD_3	
+12.5 V	+6 V	H	L	H	L	Program memory address 0 clear
		L	H	H	H	Write mode
		L	L	H	H	Verify mode
		H	x	H	H	Program inhibit mode

x: L or H

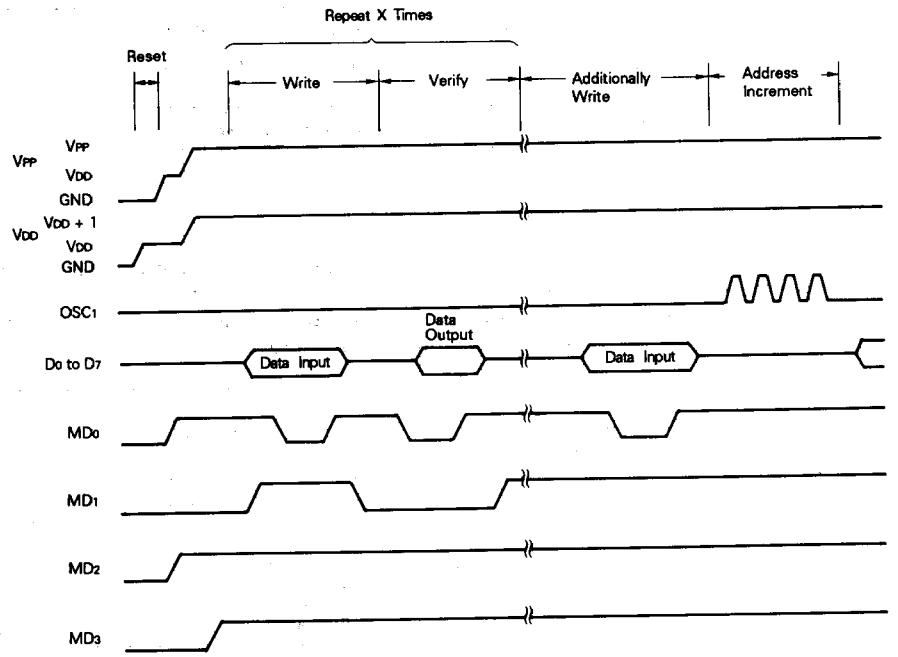
10.2 PROGRAM MEMORY WRITING PROCEDURE

The program memory writing procedure is shown below. High-speed write is possible.

(1) Pull down the pins not to be used to GND via the resistor. The OSC_1 pin at the low level.
(2) Supply 5 V to the V_{DD} pin. The V_{PP} pin at the low level.
(3) Wait 10 μs and then supply 5 V to the V_{PP} pin.
(4) Set the mode setting pin to the program memory address 0 clear mode.
(5) Supply 6 V to V_{DD} and 12.5 V to V_{PP}.
(6) Assume the program inhibit mode.
(7) Write data in the 1-ms write mode.
(8) Assume the program inhibit mode.
(9) Assume the verify mode. If written, go to (10). If not, repeat (7) to (9).

(10) Additionally write (number of times written in (7) to (9): X) × 1 ms.
(11) Assume the program inhibit mode.
(12) Update (+1) the program memory address by inputting a pulse to the OSC_1 pin 4 times.
(13) Repeat (7) to (12) up to the last address.
(14) Assume the program memory address 0 clear mode.
(15) Change the V_{DD}, V_{PP} pin voltage to 5 V.
(16) Power off.

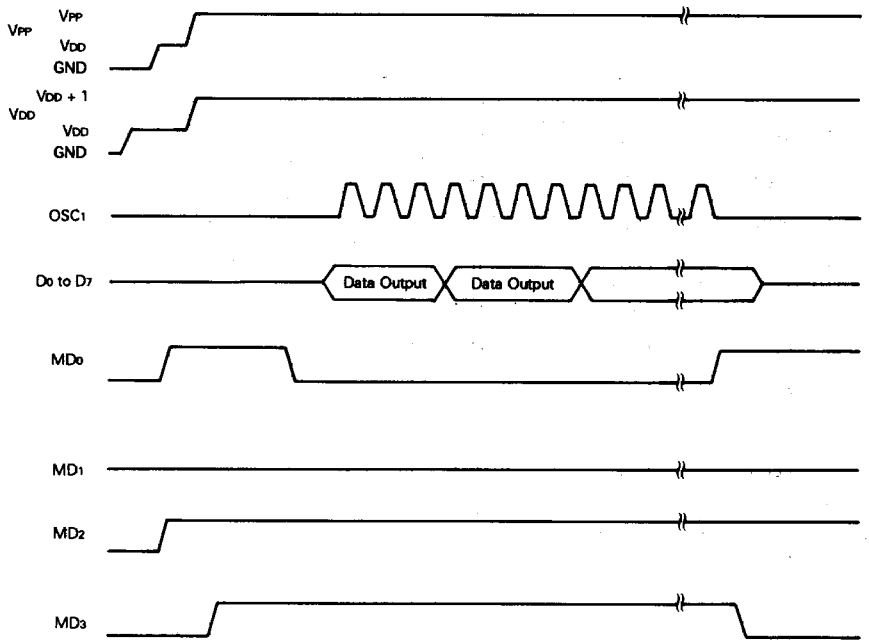
The above procedure of (2) to (12) is shown in the diagram below.



10.3 PROGRAM MEMORY READING PROCEDURE

(1) Pull down the pins not to be used to GND via the resistor. The OSC_1 pin at the low level.
(2) Supply 5 V to the V_{DD} pin. The V_{PP} pin at the low level.
(3) Wait 10 μs and then supply 5 V to the V_{PP} pin.
(4) Set the mode setting pin to the program memory address 0 clear mode.
(5) Supply 6 V to V_{DD} and 12.5 V to V_{PP}.
(6) Assume the program inhibit mode.
(7) Assume the verify mode. Output data sequentially 1 address at a time at intervals of 4 inputs when a clock pulse is input to the OSC_1 pin.
(8) Assume the program inhibit mode.
(9) Assume the program memory address 0 clear mode.
(10) Change the V_{DD}, V_{PP} pin voltage to 5 V.
(11) Power off.

The above procedure of (2) to (9) is shown in the diagram below.



11. ASSEMBLER RESERVED WORDS

Table 11-1 lists the reserved symbols defined in the μPD17P107's device file (AS17107).

Table 11-1 Reserved Symbol List

Name	Attribute	Value	R/W	Description
P0B0	FLG	0.71H.0	R/W	Port 0B, bit 0
P0B1	FLG	0.71H.1	R/W	Port 0B, bit 1
P0B2	FLG	0.71H.2	R/W	Port 0B, bit 2
P0B3*	FLG	0.71H.3	R	Value "0" fixed
P0C0	FLG	0.72H.0	R/W	Port 0C, bit 0
P0C1	FLG	0.72H.1	R/W	Port 0C, bit 1
P0C2	FLG	0.72H.2	R/W	Port 0C, bit 2
P0C3	FLG	0.72H.3	R/W	Port 0C, bit 3
P0D0	FLG	0.73H.0	R/W	Port 0D, bit 0
P0D1	FLG	0.73H.1	R/W	Port 0D, bit 1
P0D2	FLG	0.73H.2	R/W	Port 0D, bit 2
P0D3	FLG	0.73H.3	R/W	Port 0D, bit 3
BCD	FLG	0.7EH.0	R/W	BCD operation flag
PSW	MEM	0.7FH	R/W	Program status word
Z	FLG	0.7FH.1	R/W	Zero flag
CY	FLG	0.7FH.2	R/W	Carry flag
CMP	FLG	0.7FH.3	R/W	Compare flag

*: P0B3, which is not available in the μPD17P107, has been registered as a read only flag to be used as a dummy bit when using a built-in macro.

12. INSTRUCTION SETS

12.1 INSTRUCTION SET LIST

b_{14}–b_{11} \ b_{15}		0		1	
BIN	HEX				
0 0 0 0	0	ADD	r, m	ADD	m, #i
0 0 0 1	1	SUB	r, m	SUB	m, #i
0 0 1 0	2	ADDC	r, m	ADDC	m, #i
0 0 1 1	3	SUBC	r, m	SUBC	m, #i
0 1 0 0	4	AND	r, m	AND	m, #i
0 1 0 1	5	XOR	r, m	XOR	m, #i
0 1 1 0	6	OR	r, m	OR	m, #i
0 1 1 1	7	RET RETSK RORC STOP HALT NOP	 r s h 		
1 0 0 0	8	LD	r, m	ST	m, r
1 0 0 1	9	SKE	m, #i	SKGE	m, #i
1 0 1 0	A				
1 0 1 1	B	SKNE	m, #i	SKLT	m, #i
1 1 0 0	C	BR	addr	CALL	addr
1 1 0 1	D			MOV	m, #i
1 1 1 0	E			SKT	m, #n
1 1 1 1	F			SKF	m, #n

12.2 INSTRUCTION LIST

Legend

M	: One of data memory	n	: Bit position ; 4 bits
m	: Data memory address specified by (m_H, m_L) of each bank	addr	: One of program memory address ; 11 bits
m_H	: Data memory address high (row address) ; 3 bits	a_H	: Program memory address high ; 3 bits
m_L	: Data memory address low (column address) ; 4 bits	a_M	: Program memory address middle ; 4 bits
R	: One of general register specified by [(RP), r]	a_L	: Program memory address low ; 4 bits
r	: General register address low (column address) ; 4 bits	CY	: Carry flag
RP	: General register pointer	CMP	: Compare flag
PC	: Program counter	s	: Stop release condition
SP	: Stack pointer	h	: Halt release condition
STACK	: Stack specified by (SP)	[ ]	: Address of M,R
i	: Immediate data ; 4 bits	( )	: Contents of M,R

Instruction	Mnemonic	Operand	Function	Operation	Machine Code			
					Op. Code	3-Bit	4-Bit	4-Bit
Add	ADD	r,m	Add memory to register	R← (R) + (M)	00000	m_H	m_L	r
		m,#i	Add immediate data to memory	M← (M) + i	10000	m_H	m_L	i
	ADDC	r,m	Add memory to register with carry	R← (R) + (M) + (CY)	00010	m_H	m_L	r
		m,#i	Add immediate data to memory with carry	R← (M) + i+ (CY)	10010	m_H	m_L	i
Subtraction	SUB	r,m	Subtract memory from register	R← (R) − (M)	00001	m_H	m_L	r
		m,#i	Subtract immediate data from memory	M← (M) − i	10001	m_H	m_L	i
	SUBC	r,m	Subtract memory from register with borrow	R← (R) − (M) − (CY)	00011	m_H	m_L	r
		m,#i	Subtract immediate data from memory with borrow	M← (M) − i − (CY)	10011	m_H	m_L	i
Compare	SKE	m,#i	Skip if memory equal to immediate data	M−i, skip if zero	01001	m_H	m_L	i
	SKGE	m,#i	Skip if memory greater than or equal to immediate data	M−i, skip if not borrow	11001	m_H	m_L	i
	SKLT	m,#i	Skip if memory less than immediate data	M−i, skip if borrow	11011	m_H	m_L	i
	SKNE	m,#i	Skip if memory not equal to immediate data	M−i, skip if not zero	01011	m_H	m_L	i
Logic operation	AND	m,#i	Logical AND of memory and immediate data	M← (M) AND i	10100	m_H	m_L	i
		r,m	Logical AND of register and memory	R← (R) AND (M)	00100	m_H	m_L	r
	OR	m,#i	Logical OR of memory and immediate data	M← (M) OR i	10110	m_H	m_L	i
		r,m	Logical OR of register and memory	R← (R) OR (M)	00110	m_H	m_L	r
	XOR	m,#i	Logical XOR of memory and immediate data	M← (M) XOR i	10101	m_H	m_L	i
		r,m	Logical XOR of register and memory	R← (R) XOR (M)	00101	m_H	m_L	r
Transfer	LD	r,m	Load memory of register	R← (M)	01000	m_H	m_L	r
	ST	m,r	Store register to memory	(M)←R	11000	m_H	m_L	r
	MOV	m,#i	Move immediate data to memory	M←i	11101	m_H	m_L	i
Judge	SKT	m,#n	Test memory bits, then skip if all bits specified are true	CMP←0 skip if M_n=all "1"	11110	m_H	m_L	n
	SKF	m,#n	Test memory bits, then skip if all bits specified are false	CMP←0 skip if M_n=all "0"	11111	m_H	m_L	n

Instruction	Mnemonic	Operand	Function	Operation	Machine Code			
					Op. Code	3-Bit	4-Bit	4-Bit
Branch	BR	addr	Jump to the address	PC←ADDR	01100	a_H	a_M	a_L
Shift	RORC	r	Rotate register right with carry	(CY)→(R)→CY	00111	000	0111	r
Subroutine	CALL	addr	Call subroutine	SP←(SP) − 1 STACK←((PC) + 1), PC←ADDR	11100	a_H	a_M	a_L
	RET		Return to main routine from subroutine	PC←(STACK), SP←(SP) + 1	00111	000	1110	0000
	RETSK		Return to main routine from subroutine, then skip unconditionary	PC←(STACK), SP←(SP) + 1 and skip	00111	001	1110	0000
Other	STOP	s	Stop clock	STOP	00111	010	1111	s
	HALT	h	Halt the CPU, restart by condition h	HALT	00111	011	1111	h
	NOP		No operation	No Operation	00111	100	1111	0000

13. ELECTRIC CHARACTERISTICS

ABSOLUTE MAXIMUM RATINGS (T_a = 25 °C)

Supply Voltage	V_{DD}			−0.3 to +7.0	V
Supply Voltage	V_{PP}			−0.3 to +13.5	V
Input Voltage	V_I	P0C, P0D, $\overline{\text{RESET}}$		0.3 to V_{DD} +0.3	V
		P0B		−0.3 to +11	V
Output Voltage	V_O	P0C, P0D		0.3 to V_{DD} +0.3	V
		P0B		−0.3 to +11	V
High-level Output Amperage	I_{OH}	P0B, P0C, P0D per pin		−5	mA
		Total for all pins		−15	mA
Low-level Output Amperage	I_{OL}	P0B, P0C, P0D per pin		30	mA
		Total for all pins		100	mA
Operating Temperature	T_{opt}			−40 to +85	°C
Storage temperature	T_{stg}			−65 to +150	°C
Power Dissipation	P_d	T_a = 85 °C	16 pin DIP	400	mW
			16 pin SOP	190	mW

CAPACITY (T_a = 25 °C, V_{DD} = 0 V)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITION
Input Capacity	C_{IN}			15	pF	f = 1 MHz, 0 V at other than measured pins
Input/Output Capacity	C_{IO}			15	pF	

DC CHARACTERISTICS (T_a = −40 to +85 °C, V_{DD} = 2.5 to 6.0 V)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITION	
High-level Input Voltage	V_{IH1}	0.7 V_{DD}		V_{DD}	V	Other than specified below.	
	V_{IH2}	0.8 V_{DD}		V_{DD}	V	P0B, $\overline{RESET}$	
	V_{IH3}	0.8 V_{DD}		9	V	P0B*	
	V_{IH4}	V_{DD} - 0.5		V_{DD}	V	OSC_1	
Low-level Input Voltage	V_{IL1}	0		0.3 V_{DD}	V	Other than specified below.	
	V_{IL2}	0		0.2 V_{DD}	V	P0B, $\overline{RESET}$	
	V_{IL3}	0		0.5	V	OSC_1	
P0C, D High-level Output Voltage	V_{OH}	V_{DD} - 2.0			V	V_{DD} = 4.5 to 6.0 V I_{OH} = −2 mA	
		V_{DD} - 1.0			V	I_{OH} = −200 μA	
P0B, C, D Low-level Input Voltage	V_{OL}			2.0	V	V_{DD} = 4.5 to 6.0 V I_{OL} = 15 mA	
				0.5	V	I_{OL} = 600 μA	
P0B, C, D High-level Input Leak Current	I_{LIH1}			5	μA	V_{IN} = V_{DD}	
	I_{LIH2}			10	μA	V_{IN} = 9 V*	
P0B, C, D Low-level Input Leak Current	I_{LIL}			−5	μA	V_{IN} = 0 V	
P0B, C, D High-level Output Leak Current	I_{LOH1}			5	μA	V_{OUT} = V_{DD}	
	I_{LOH2}			10	μA	V_{OUT} = 9 V*	
P0B, C, D Low-level Output Leak Current	I_{LOL}			−5	μA	V_{OUT} = 0 V	
Supply Amperage	I_{DD1}		0.4	1.2	mA	Run mode	V_{DD} = 5 V ±10 % f_{CC} = 1.0 MHz ±20 %
			50	150	μA		V_{DD} = 3 V ±10 % f_{CC} = 250 kHz ±20 %
	I_{DD2}		0.3	0.9	mA	HALT mode	V_{DD} = 5 V ±10 % f_{CC} = 1.0 MHz ±20 %
			40	120	μA		V_{DD} = 3 V ±10 % f_{CC} = 250 kHz ±20 %
	I_{DD3}		0.1	10	μA	STOP mode	V_{DD} = 5 V ±10 %
			0.1	5	μA		V_{DD} = 3 V ±10 %

*: If N-ch open-drain input/output selected.

LOW-SUPPLY VOLTAGE DATA HOLDING CHARACTERISTICS IN DATA MEMORY STOP MODE (T_a = −40 to +85 °C)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITION
Data Holding Supply Voltage	V_{DDDR}	2.0		6.0	V	
Data Holding Supply Amperage	I_{DDDR}		0.1	5.0	μA	V_{DDDR} = 2.0 V
Release Signal Set Time	t_{SREL}	0			μs	

AC CHARACTERISTICS (T_a = −40 to +85 °C, V_{DD} = 2.5 to 6.0 V)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITION
Internal Clock Cycle Time	T_{CY}	6.6		160	μs	V_{DD} = 4.5 to 6.0 V
		26.6		160	μs	
$P0B_0$, $P0B_1$, High/Low Level Width	T_{PBH} T_{PBL}	10			μs	
$\overline{RESET}$, High/Low Level Width	T_{RSH} T_{RSL}	10			μs	

DC PROGRAMMING CHARACTERISTICS (T_a = 25 °C, V_{DD} = 6.0 ±0.25 V, V_{PP} = 12.5 ±0.5 V)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITION
High-Level Input Voltage	V_{IH1}	0.7 V_{DD}		V_{DD}	V	Other than OSC_1
	V_{IH2}	V_{DD} - 0.5		V_{DD}	V	OSC_1
Low-Level Input Voltage	V_{IL1}	0		0.3 V_{DD}	V	Other than OSC_1
	V_{IL2}	0		0.4	V	OSC_1
Input Leak Current	I_{LI}			10	μA	V_{IN} = V_{IL} or V_{IH}
High-Level Output Voltage	V_{OH}	V_{DD} - 1.0			V	I_{OH} = −1 mA
Low-Level Output Voltage	V_{OL}			0.4	V	I_{OL} = 1.6 mA
V_{DD} Supply Current	I_{DD}			30	mA	
V_{PP} Supply Current	I_{PP}			30	mA	MD0 = V_{IL}, MD1 = V_{IH}

NOTE 1: V_{PP} must not be a minimum of +13.5 V including overshoot.
2: Impress V_{DD} before V_{PP} and break it after V_{PP}.

AC PROGRAMMING CHARACTERISTICS (T_a = 25 °C, V_{DD} = 6.0 ±0.25 V, V_{PP} = 12.5 ±0.5 V)

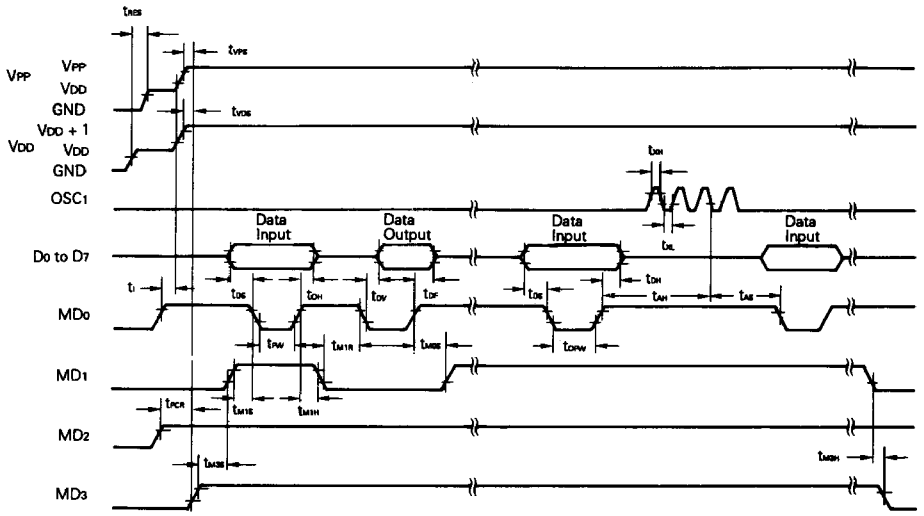
CHARACTERISTICS	SYMBOL	*1	MIN.	TYP.	MAX.	UNIT	CONDITION
Address Set-Up Time *2 (for MD0 ↓)	t_{AS}	t_{AS}	2			μs	
MD1 Set-Up Time (for MD0 ↓)	t_{M1S}	t_{OES}	2			μs	
Data Set-Up Time (for MD0 ↓)	t_{DS}	t_{DS}	2			μs	
Address Hold Time *2 (for MD0 ↑)	t_{AH}	t_{AH}	2			μs	
Data Hold Time (for MD0 ↑)	t_{DH}	t_{DH}	2			μs	
MD0 ↑ → Data Output Float Delay Time	t_{DF}	t_{DF}	0		130	ns	
V_{PP} Set-Up Time (for MD3 ↑)	t_{VPS}	t_{VPS}	2			μs	
V_{DD} Set-Up Time (for MD3 ↑)	t_{VDS}	t_{VCS}	2			μs	
Initial Program Pulse Width	t_{PW}	t_{PW}	0.95	1.0	1.05	ms	

CHARACTERISTICS	SYMBOL	*1	MIN.	TYP.	MAX.	UNIT	CONDITION
Additional Program Pulse Width	t_{OPW}	t_{OPW}	0.95		21.0	ms	
MD0 Set-Up Time (for MD1 ↑)	t_{MOS}	t_{CES}	2			μs	
MD0 ↓→ Data Output Delay Time	t_{DV}	t_{DV}			1	μs	MD0 = MD1 = V_{IL}
MD1 Hold Time (for MD0 ↑)	t_{M1H}	t_{DEH}	2			μs	$t_{M1H} + t_{M1R} \geq 50$ μs
MD1 Recover Time (for MD0 ↓)	t_{M1R}	t_{OR}	2			μs	
Program Counter Reset Time	t_{PCR}	-	10			μs	
OSC_1 Input High/Low Level Width	t_{XH}, t_{XL}	-	0.42			μs	
OSC_1 Input Frequency	f_{OSC}	-			1.2	MHz	
Initial Mode Set Time	t_I	-	2			μs	
MD3 Set-Up Time (for MD1 ↑)	t_{M3S}	-	2			μs	
MD3 Hold Time (for MD1 ↓)	t_{M3H}	-	2			μs	
MD3 Set-Up Time (for MD0 ↓)	t_{M3SR}	-	2			μs	At program memory read
Address *2 → Data Output Delay Time	t_{DAD}	t_{ACC}	2			μs	At program memory read
Address *2 → Data Output Hold Time	t_{HAD}	t_{OH}	0		130	ns	At program memory read
MD3 Hold Time (for MD0 ↑)	t_{M3HR}	-	2			μs	At program memory read
MD3 ↓→ Data Output Float Delay Time	t_{DFR}	-	2			μs	At program memory read
Reset Set-Up Time	t_{RES}		10			μs	

*1: A symbol of the corresponding μPD27C256.

*2: The internal address signal is incremented (+1) at the 3rd OSC_1 input falling and is not connected to a pin.

PROGRAM MEMORY WRITING TIMING



PROGRAM MEMORY READING TIMING